

Design and Fabrication of Band Pass Filter (BPF) Based on Substrate Integrated Waveguide (SIW) Technology for Communication Applications

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Abstract-

In this paper a new filter is constructed by embedding two semi-circular slots have been in the SIW structure for use in X-band applications. The insertion of these slots has successfully led to the compact size and the wide bandwidth. The cavity dimensions are $9.94 \times 13.09 \text{ mm}^2$ while the overall filter dimensions are $26.6 \times 14 \text{ mm}^2$ using a substrate with relative permittivity of 2.2 and thickness of 0.245 mm. The resulting structure exhibits a return loss less than -15 dB and insertion loss approaching to -0.26 dB over the passband, while a fractional bandwidth of about 68.4% centered at 11.7 GHz. An acceptable agreement between the experimental and simulation results. The compact size offered by this filter makes it a suitable for use in designing microwave circuits. The simulation and performance evaluation of the proposed filter have been carried out using Microwave Studio Suite of Computer Simulation Technology (CST).

الخلاصة-

في هذا البحث، تم تنفيذ مرشح جديد وذلك بتضمين شقوق شبه دائرية الشكل في تركيبية الـ (SIW) لغرض استخدامه في تطبيقات الـ (X-band). ان تضمين هذه الشقوق في هذا المرشح ادى الى الحصول على حجم مصغر وحزمة عريضة. ابعاد المرشح هي 9.94×13.09 ملم مربع في حين الابعاد الكلية 26.6×14 ملم مربع وذلك باستخدام قاعدة اساس ذات سماحية نسبية 2.2 وسماك 0.254 ملم. لقد اظهرت النتائج ان المرشح يتمتع بخسائر ارجاع اقل من -15 dB وخسائر داخلية تقترب من -0.26 dB على طول الحزمة والنسبة المئوية لحزمة العمل بلغت 68.4% وقيمة التردد الوسطي هي 11.7 GHz. وقد تبين من خلال مقارنة النتائج العملية مع نتائج المحاكاة ان هناك تطابق تطابق مقبول جدا. ان الميزات التي وردت في اعلاه جعلت هذا المرشح ملائما للعمل في تصميم دوائر انظمة الموجات الدقيقة. ان عمليات المحاكاة وتقييم الاداء لهذا المرشح المقترح قد نفذت باستخدام الحقيبة البرمجية المعروفة بـ (MWS CST).

I. INTRODUCTION

The waveguide can be characterized by the possibility of dealing with handling high power capacity, high quality factor and a few losses, but due to the large size, waveguides cannot be familiar in planar devices environment. On the contrary, one find that the planar structures characterized by their small size and ease of manufacturing and ease of compatibility with integrated circuits and other tools. However, we still encounter the difficulty of dealing with high capacity and high losses. The introduction of the substrate integrated waveguide, SIW, represents a planar structure which combines the good features of the previous structures.

An SIW is a synthesized non-planar waveguide that is transformed into planar form. It can then be integrated into any planar dielectric substrate with any planar fabrication or processing technique. This will include the printed circuit boards (PCBs), and low-temperature co-fired ceramic (LTCC) technologies, among others [1]. The basic idea of the substrate integrated waveguide technique is the allocation of rows of cylindrical holes with certain radius and specific spacing. This led to emerging guided-wave structure and it looks like two parallel walls that have a specific spacing in which EM waves are well confined [1]. The purpose of the application of this technique is to make the planar structures behave as a waveguide. Therefore; all the concepts of waveguide theory can be applied to these planar structures.

Due to the advantages offered by the SIW techniques, it has been attractive for microwave circuits and antenna designers. To illustrate more, the published research works can be classified into more than one category depending on how this technique has been applied. The first category includes distribution of via holes linearly on the sides of the substrate [2-5]. The second category included via holes distribution in particular certain pattern on the top layer of the planar structure [6-11]. While in the third category, defected ground structures, DGSs, and complementary single split resonators CSSRs have been applied in the ground planes of the SIW structures included in the previous two categories [12-16].

In this paper, a semi-circular slots loaded SIW based BPF is presented. The proposed BPF offers a compact size and wide bandwidth.

II. FILTER DESIGN

In this paper the structure of the proposed SIW BPF represents an improvement of that reported in the literature [17]. The relationship between the cut-off frequency, f_c , and the dimensions of any waveguide filled with a dielectric material can be related together, and this relationship can be considered as the starting points of a SIW design. For a rectangular waveguide, the cut-off frequency of a dominant TE_{mn} mode is given by [18]:

$$f_c = \frac{c}{2\pi} \sqrt{\left(\frac{m\pi}{a}\right)^2 + \left(\frac{n\pi}{b}\right)^2} \quad (1)$$

where c is the speed of light in free space, m and n are mode numbers, a and b are the longer and the shorter dimensions of the waveguide respectively. For the dominant TE_{10} mode, Equation 1 is simplified to:

$$f_c = \frac{c}{2a} \quad (2)$$

For dielectric filled waveguide with same cut off frequency, dimension " a_d " is found to be:

$$a_d = \frac{a}{\sqrt{\epsilon_R}} \quad (3)$$

where ϵ_{eff} is the effective dielectric constant, and can be calculated by empirical expressions reported in the literature [19].

Having determined the dimension " a " for the dielectric filled waveguide; we can now pass to an empirical design equation of the SIW correlating its width, a_s , and is given by [20]:

$$a_s = a_d + \frac{d^2}{0.95p} \quad (4)$$

where d is the diameter of the vias, and p is the center to center separation between the vias along the longitudinal direction. A general rule of thumb for the choice of d and p is given in (5) and (6), respectively [20]:

$$d < \lambda_g/5 \quad (5)$$

$$p < 2d \quad (6)$$

The proposed filter is constructed by inserting two slots like semi-circular in the SIW structure as shown Figure 1.

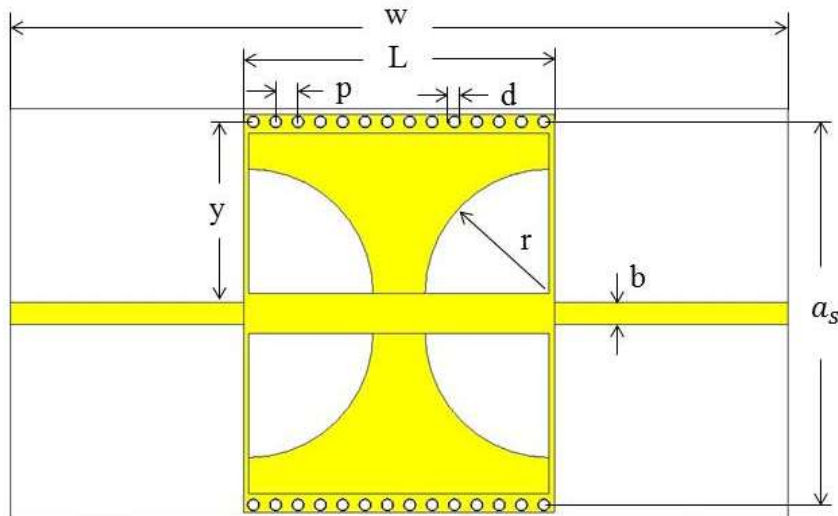


Figure 1: The front view of the simulated SIW BPF.

III. PARAMETRIC STUDY AND SIMULATION RESULTS

The proposed SIW cavity dimensions are $9.94 \times 13.09 \text{ mm}^2$ while the overall dimensions are $26.6 \times 14 \text{ mm}^2$ as shown in Figure 1. using a substrate with relative permittivity of 2.2 and thickness of 0.245 mm. The detailed and optimum dimensions of the proposed filter are illustrated in Table 1.

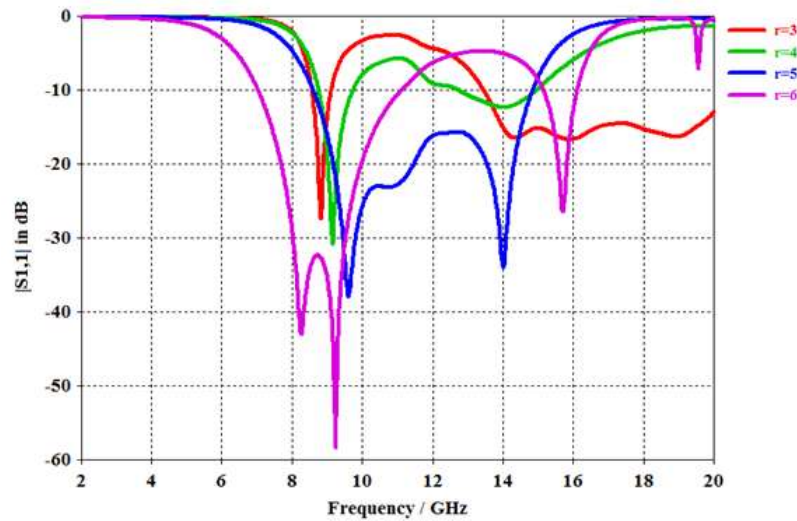
Table 1 Summary of the dimensions of the proposed filter structure

Parameter	L	w	a_s	r	b	y	d	p
Value (mm)	10.625	26.625	13.09	5	0.76	6.165	0.50	0.765

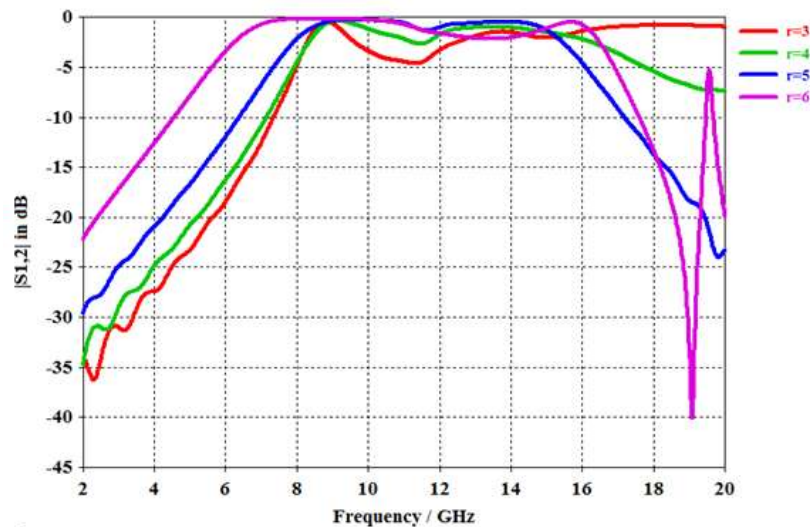
Many parameters have tested to get more insight about their effects on the performance of proposed filter.

It is found that the most influential of these factors is the radius of the half-circular slot. A parametric study has been conducted to explore the effect of the embedded semi-circular slot radius r on the presented filter performance. The effect of varying the slot radius r , while keeping the other filter parameters unchanged, has been shown in Figures 2 (a) and (b).

Examining the results of Figure 2, it is clear that the increase of r leads to reduce the lower cut-off frequency. As r becomes larger, up to r equal to 5 mm, this will expand the filter bandwidth. Beyond this value reduction of lower cut-off frequency continues. However, the effect of varying r on the filter performance can be described as follows. As r increases, the position of the lower transmission zero has been shifted away from the lower edge cut-off frequency resulting in a low selectivity and roll-off rate. Furthermore, the increase of r makes the upper transmission zero approaches the upper edge cut-off frequency resulting in higher selectivity and higher roll-off rate at the upper passband. The resulting increase in the filter bandwidth is at the expense of the in-band performance.



(a)



(b)

Figure 2: The simulated S_{11} and S_{12} responses of the proposed BPF with r as a parameter.

There must be some compromise between the various requirements of the wide bandwidth, higher selectivity at both the lower and the upper edges of the passband, besides the low ripple in the filter passband. Figure 3 shows the performance responses of the resulting filter responses with the dimensions summarized in Table 1. The filter have exhibited a return loss less than -15 dB at the center of the passband, insertion loss

approaching to -0.26 dB over the passband and offers a fractional bandwidth of about 68.4% centered at 11.7 GHz.

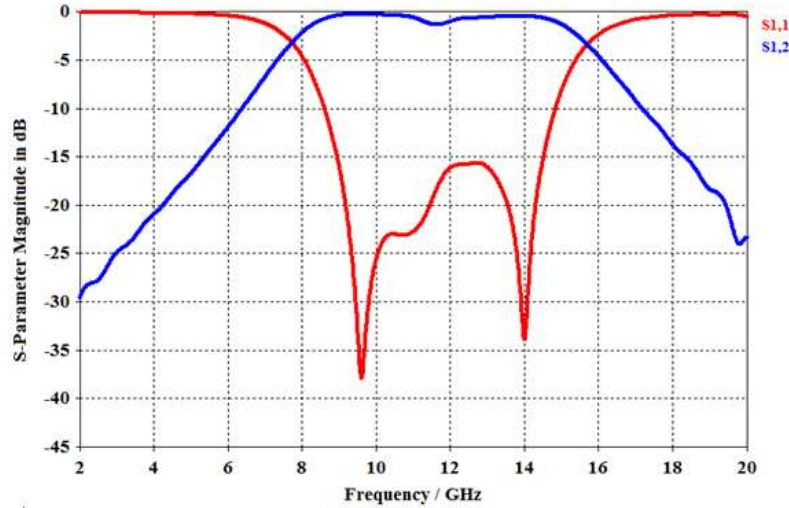


Figure 3: The simulated S_{11} and S_{12} responses of the proposed BPF with $r = 5$ mm.

IV. FABRICATION AND MEASUREMENT

Figure 4 shows the photograph of the fabricated prototype of the proposed filter. The performance of the designed filter was measured using an Anritsu MS4642A Vector Network Analyzer (VNA).

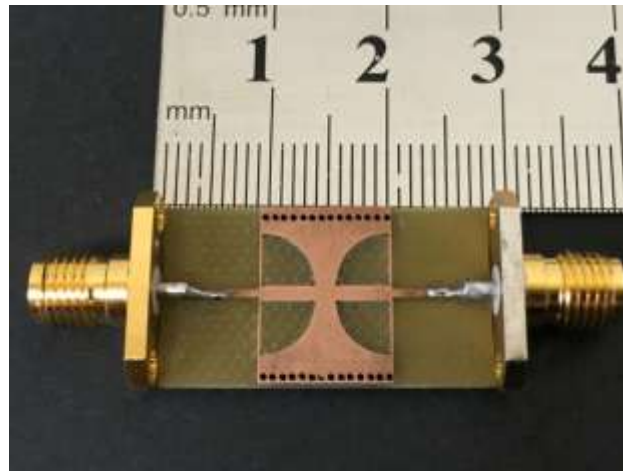


Figure 4: Photograph of the fabricated prototype of the circular-shaped slots SIW BPF.

The measured results agree with the EM simulation results in terms of S-parameter as illustrated in Figure 5. However, measured insertion loss at 11.7 GHz is

about -1.5 dB which is somewhat higher than the simulation results. This is because connector losses and unexpected material losses that could not be accounted in the simulations. Good out-of-band rejection is achieved due to two TZs located at 16.4 and 18.3 GHz. The frequency band is reduced to 12% compared with the simulated results, but the center frequency is not affected. This is probably due to the unspecified values of a relative permittivity (ϵ_r) and possible fabrication errors. On the other hand, measured return loss is better than -20 dB and this return loss value is quite sufficient for matching.

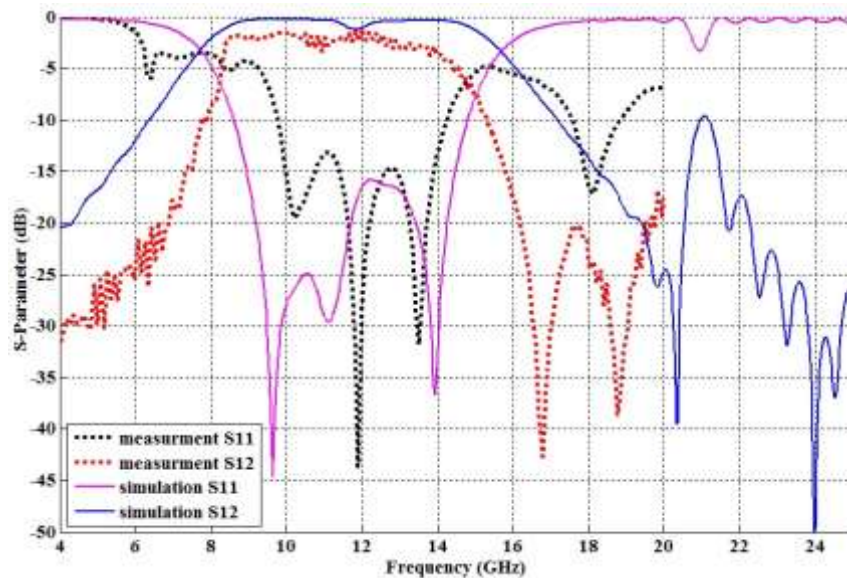


Figure 5: Comparison between the simulated (solid) and the measured (dashed) S-parameters for the fabricated circular-shaped slots SIW BPF.

V. CONCLUSIONS

A new compact substrate integrated waveguide (SIW) band pass filter (BPF) is presented in this paper as a candidate for use in wide bandwidth X-band applications. Two semi-circular slots have been embedded in the structure from the input and the output sides. The simulation and performance evaluation of the proposed filter have been exhibited a return loss less than -15 dB, insertion loss approaching to -0.26 dB over the pass band and offers a fractional bandwidth of about 68.4% centered at 11.7 GHz. A parametric study reveals that the insertion of these slots has successfully led to the compact size and the wide bandwidth. An acceptable agreement between the experimental and simulation results. The compact size offered by this filter makes it a suitable for use in designing microwave and millimeter-wave circuits.

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